SuperMOS –SOT23-6L 20V BV_{DSS}, 13.5mΩ $R_{DS(on)}$, N-channel MOSFET

1. Description

The CJL8810-ES is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product CJL8810-ES is Pb-free.

2. Features

- 20V, $R_{DS(ON)}$=13.5mΩ(Typ.), V_{GS}=4.5V
  $R_{DS(ON)}$=16.5mΩ(Typ.), V_{GS}=2.5V
- Use trench MOSFET technology
- High density cell design for low $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

3. Applications

- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel Size
CJL8810-ES	SOT23-6L	.L8810	Halogen free	Tape & Reel	3,000 PCS	UL 94V-0	7 inches

Table-1 Ordering information

5. Pin Configuration and Functions

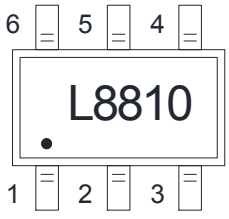
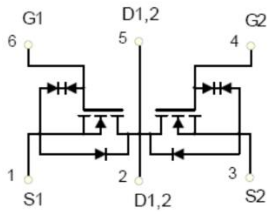
Pin	Function	Outline	Circuit Diagram
6	Gate1		
1	Source1		
2/5	Drain		
4	Gate2		
3	Source2		

Table-2 Pin configuration

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 ℃ ambient temperature unless otherwise specified.

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		BV_{DSS}	20	V
Gate-Source Voltage		V_{GS}	±10	V
Continuous Drain Current	T_A=25°C	I_D	7.6	A
	T_A=75°C		5.9	
Maximum Power Dissipation	T_A=25°C	P_D	1.5	W
	T_A=75°C		0.9	
Pulsed Drain Current		I_{DM}	30.4	A
Operating Junction Temperature		T_J	150	°C
Lead Temperature		T_L	260	°C
Storage Temperature Range		T_{stg}	-55 to 150	°C

Thermal resistance ratings

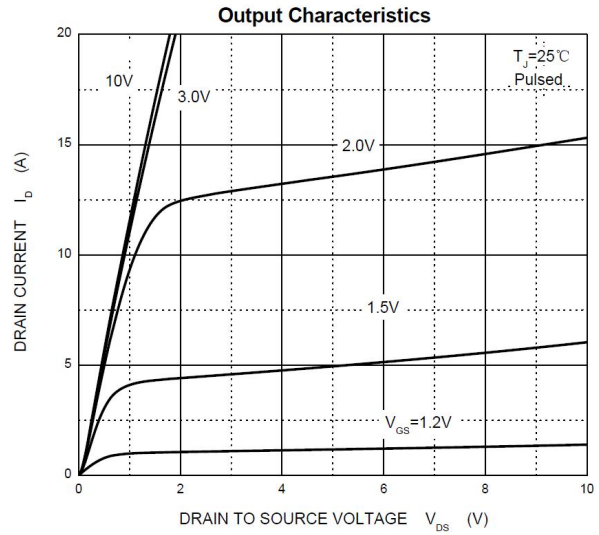
Single Operation					
Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance	t ≤ 10 s	$R_{\theta JA}$		83.3	°C/W

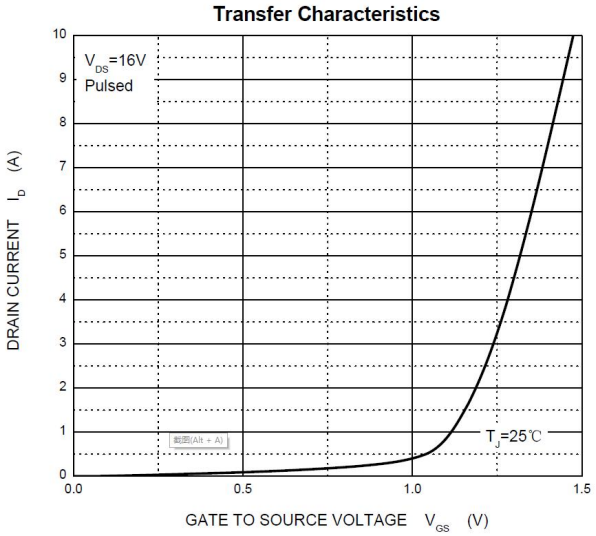
Electrical Characteristics

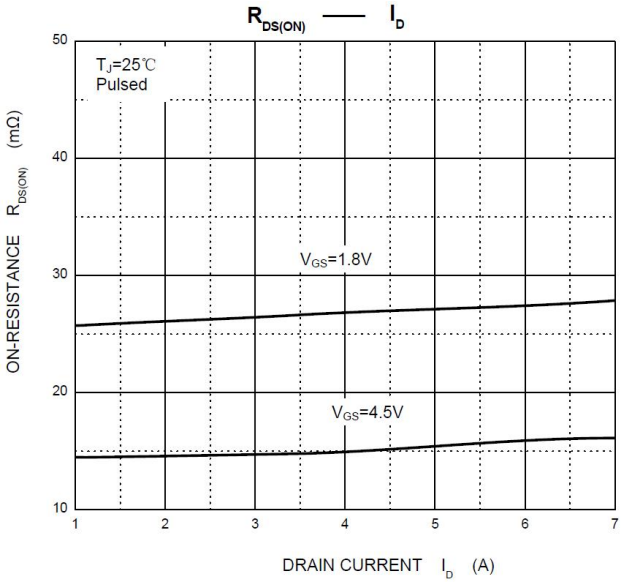
At TA = 25℃ unless otherwise specified

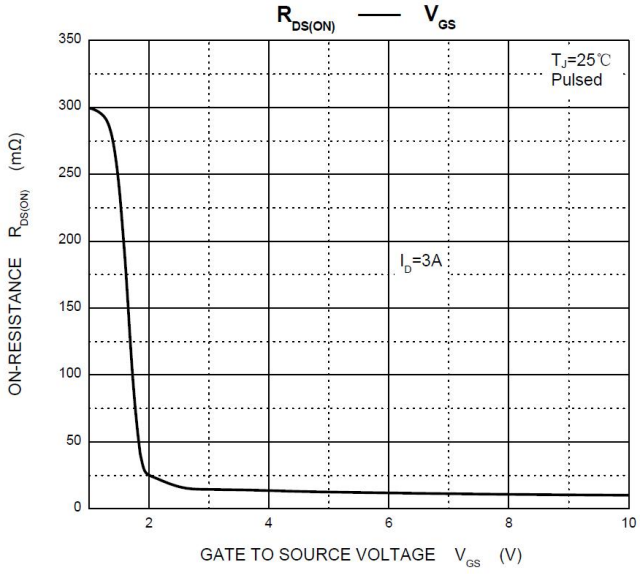
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250uA	20			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=20V, V_{GS}=0V			1.0	uA
Gate-to-source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS}=±10V			±10	uA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS}=V_{DS}, I_D=250uA	0.5	0.7	0.9	V
Drain-to-source On-resistance	$R_{DS(on)}$	V_{GS}=4.5V, I_D=5A		13.5	17	mΩ
		V_{GS}=2.5V, I_D=5A		16.5	23	
Forward Trans conductance	g_{FS}	V_{DS}=5.0V, I_D=5A			40	S
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C_{ISS}	V_{GS}=0V, f=1MHz, V_{DS}=10V		1150		pF
Output Capacitance	C_{OSS}			165		
Reverse Transfer Capacitance	C_{RSS}			150		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS}=4.5V, V_{DS}=10V, I_D=5A		15		nC
Gate-to-Source Charge	Q_{GS}			1		
Gate-to-Drain Charge	Q_{GD}			3.5		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(ON)}$	V_{GS}=4.5V, V_{DS}=10V, R_L=1.35Ω, R_G=3Ω		8		ns
Rise Time	t_r			11		
Turn-Off Delay Time	$t_{d(OFF)}$			50		
Fall Time	t_f			18		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	V_{GS}=0V, I_S=1A	0.45		1.5	V

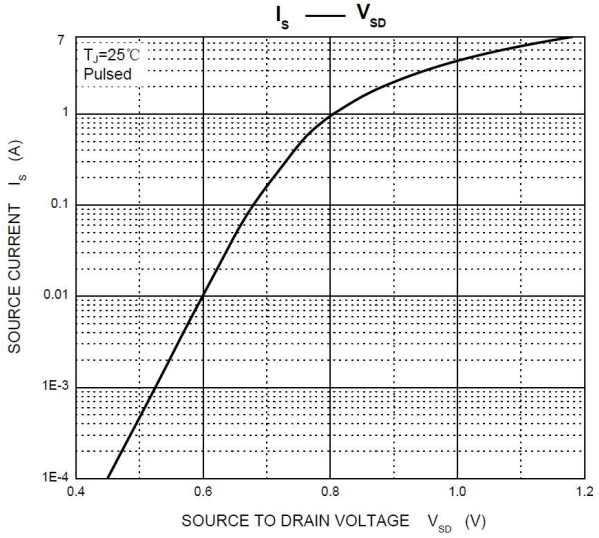
7. Typical Characteristic

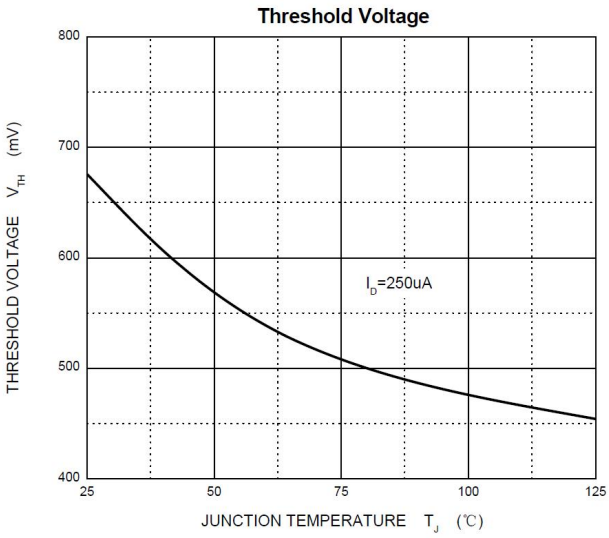




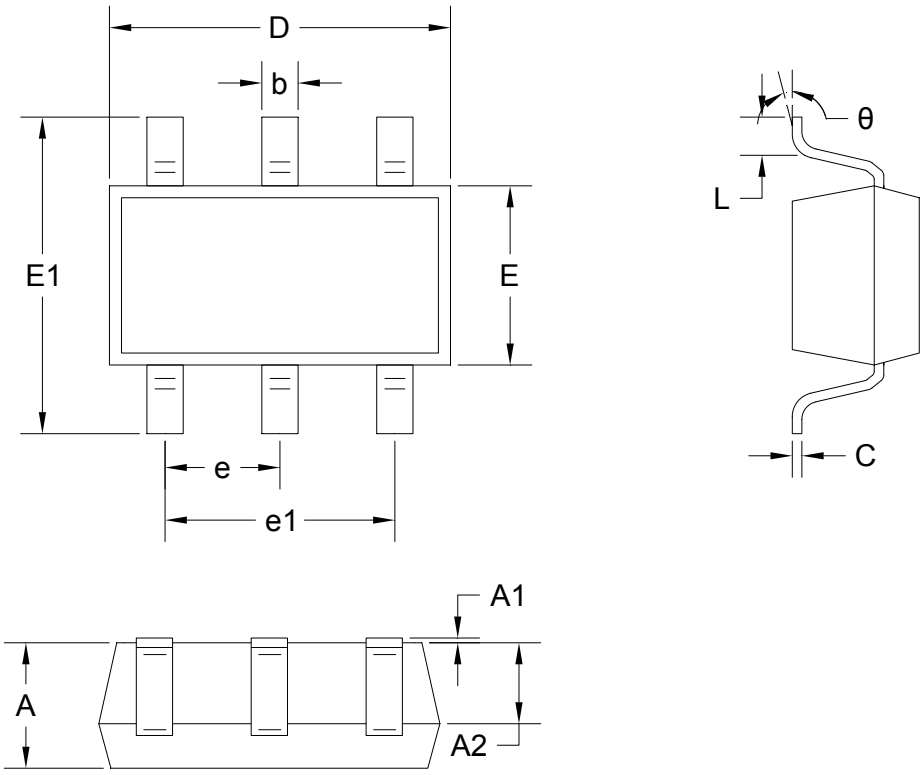








8. Dimension (SOT23-6L)



Unit: mm

Symbol		A	A1	A2	b	c	D
Spec	Min	1.050	0.000	1.050	0.300	0.100	2.820
	Max	1.250	0.100	1.150	0.500	0.200	3.020
Symbol		E	E1	e	e1	L	θ
Spec	Min	1.500	2.650	0.950BSC	1.800	0.300	0°
	Max	1.700	2.950		2.000	0.600	8°

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